

| Ref # | Hits | Search Query   | DBs   | Default Operator | Plurals | Time Stamp       |
|-------|------|--|---|------------------|---------|------------------|
| L1    | 7129 | @ad<="20030915" and (257/382).ccls. or (257/532).ccls. or (257/755).ccls. or (257/763).ccls. or (257/E21.507).ccls. or (257/E21.59).ccls. or (257/E21.593).ccls. or (257/E21.66).ccls. | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/04/15 14:41 |
| L2    | 3176 | @ad<="20030915" and (438/238).ccls. or (438/586).ccls.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/04/15 14:41 |
| L3    | 123  | @ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'peripheral'   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/04/15 14:43 |
| L4    | 123  | @ad<="20030915" and 'SRAM' same 'polysilicon layers' and 'cell' and 'peripheral'   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/04/15 14:43 |
| S1    | 9    | @ad<="20030915" and 'cell' same 'logic' same 'cell gate oxide' and 'polysilicon'   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/06 16:03 |
| S2    | 30   | @ad<="20030915" and 'SRAM' same 'dual' with 'polysilicon'  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/06 16:40 |
| S3    | 6963 | @ad<="20030915" and (257/382).ccls. or (257/532).ccls. or (257/755).ccls. or (257/763).ccls. or (257/E21.507).ccls. or (257/E21.59).ccls. or (257/E21.593).ccls. or (257/E21.66).ccls. | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/04/15 14:41 |
| S4    | 3125 | @ad<="20030915" and (438/238).ccls. or (438/586).ccls.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2005/04/15 14:41 |
| S5    | 1    | "6080647".PN.  | USPAT;<br>USOCR   | OR               | ON      | 2004/12/06 16:19 |
| S6    | 1    | "5866451".PN.  | USPAT;<br>USOCR   | OR               | ON      | 2004/12/06 16:19 |
| S7    | 5938 | @ad<="20030915" and (438/621).ccls. or (438/655).ccls. or (438/656).ccls. or (438/657).ccls. or (438/253).ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR               | ON      | 2004/12/06 16:29 |
| S8    | 1    | "6294420".PN.  | USPAT;<br>USOCR   | OR               | ON      | 2004/12/06 16:22 |

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| S9  | 1    | "6177340".PN.   | USPAT;<br>USOCR   | OR | ON | 2004/12/06 16:22 |
| S10 | 2030 | @ad<="20030915" and (438/585).<br>ccls. or (438/152).ccls. or<br>(438/594).ccls. or (438/734).ccls.                           | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/06 16:29 |
| S12 | 159  | @ad<="20030915" and 'SRAM'<br>same 'polysilicon layers' and 'cell'<br>and 'logic'   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/06 17:21 |
| S13 | 122  | @ad<="20030915" and 'SRAM'<br>same 'polysilicon layers' and 'cell'<br>and 'peripheral'  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2005/04/15 14:42 |
| S14 | 2188 | @ad<="20030915" and (438/253).<br>ccls.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/06 17:03 |
| S15 | 174  | @ad<="20030915" and 'SRAM'<br>same 'first polysilicon' and 'second<br>polysilicon'  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/06 17:22 |
| S16 | 669  | @ad<="20030915" and 'SRAM'<br>and 'first polysilicon' and 'second<br>polysilicon'   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/06 17:22 |
| S17 | 543  | @ad<="20030915" and 'SRAM'<br>and 'first polysilicon' and 'second<br>polysilicon' and 'cell' and 'device'                     | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/06 17:23 |
| S18 | 304  | @ad<="20030915" and 'SRAM'<br>and 'first polysilicon' and 'second<br>polysilicon' and 'cell' same 'device'<br>same 'region'   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 08:28 |
| S19 | 653  | @ad<="20030915" and 'SRAM'<br>same 'memory' and 'peripheral'<br>and 'polysilicon layers'                                      | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 08:29 |
| S20 | 301  | @ad<="20030915" and 'SRAM'<br>and 'first polysilicon' and 'second<br>polysilicon' and 'memory' same<br>'device' same 'region' | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 08:29 |

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| S21 | 9   | @ad<="20030915" and 'SRAM'<br>same 'memory' same 'peripheral'<br>same 'polysilicon layers' | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 08:29 |
| S22 | 811 | @ad<="20030915" and (257/903).<br>ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 12:35 |
| S23 | 324 | @ad<="20030915" and<br>(257/380-381).ccls.   | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 12:40 |
| S24 | 138 | @ad<="20030915" and (257/385).<br>ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 12:41 |
| S25 | 260 | @ad<="20030915" and (257/756).<br>ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 12:41 |
| S26 | 501 | @ad<="20030915" and (438/647).<br>ccls. or (438/657).ccls.                                 | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 12:43 |
| S27 | 196 | @ad<="20030915" and (438/630).<br>ccls.  | US-PGPUB;<br>USPAT;<br>EPO; JPO;<br>DERWENT;<br>IBM_TDB | OR | ON | 2004/12/07 12:45 |